

TOSHIBA THYRISTOR SILICON PLANAR TYPE

SF8G41A, SF8J41A

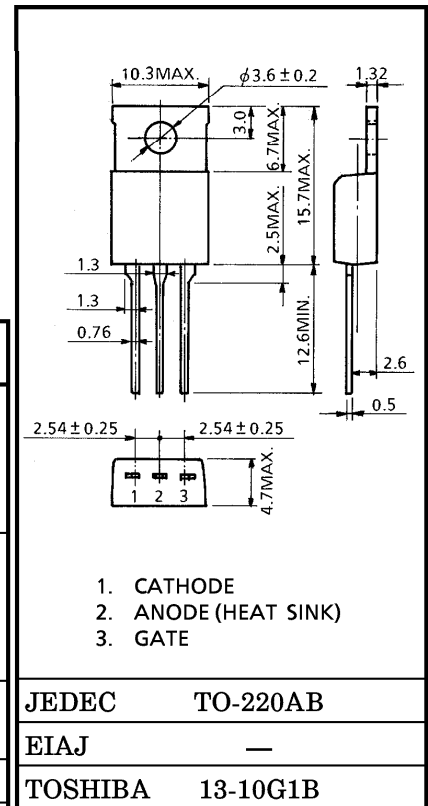
MEDIUM POWER CONTROL APPLICATIONS

Unit in mm

- Repetitive Peak Off-State Voltage : V_{DRM} } = 400, 600V
 Repetitive Peak Reverse Voltage : V_{RRM} }
- Average On-State Current : $I_T(AV) = 8A$
- Gate Trigger Current : $I_{GT} = 15mA (MAX.)$

MAXIMUM RATINGS

CHARACTERISTIC		SYMBOL	RATINGS	UNIT
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	SF8G41A	V_{DRM}	400	V
	SF8J41A	V_{RRM}	600	
Non-Repetitive Peak Reverse Voltage (Non-Repetitive < 5ms, $T_j = 0 \sim 125^\circ C$)	SF8G41A	V_{RSM}	500	V
	SF8J41A		720	
Average On-State Current (Half Sine Waveform $T_c = 83^\circ C$)		$I_T(AV)$	8	A
R.M.S On-State Current		$I_T(RMS)$	12.6	A
Peak One Cycle Surge On-State Current (Non-Repetitive)		I_{TSM}	120 (50Hz)	A
			132 (60Hz)	
I^2t Limit Value		I^2t	72	A^2s
Critical Rate of Rise of On-State Current		di/dt	100	$A/\mu s$
Peak Gate Power Dissipation		P_{GM}	5	W
Average Gate Power Dissipation		$P_G(AV)$	0.5	W
Peak Forward Gate Voltage		V_{FGM}	10	V
Peak Reverse Gate Voltage		V_{RGM}	-5	V
Peak Forward Gate Current		I_{GM}	2	A
Junction Temperature		T_j	-40~125	$^\circ C$
Storage Temperature Range		T_{stg}	-40~125	$^\circ C$



Weight : 2g

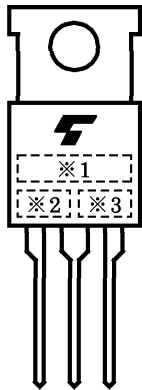
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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

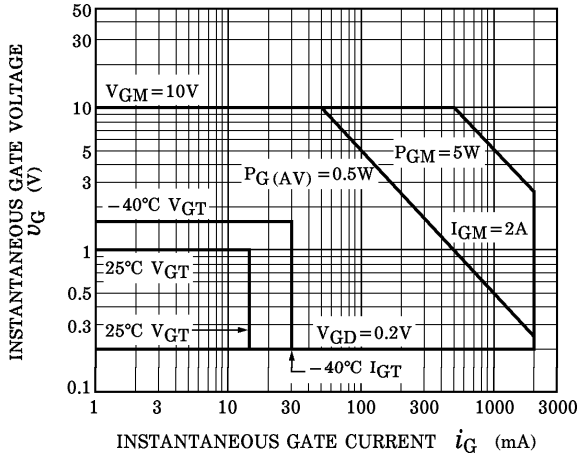
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	MAX.	UNIT
Repetitive Peak Off-State Current and Repetitive Peak Reverse Current	I_{DRM} I_{RRM}	$V_{DRM} = V_{RRM} = \text{Rated}$	—	10	μA
Peak On-State Voltage	V_{TM}	$I_{TM} = 25\text{A}$	—	1.6	V
Gate Trigger Voltage	V_{GT}	$V_D = 6\text{V}, R_L = 10\Omega$	—	1.0	V
Gate Trigger Current	I_{GT}		—	15	mA
Gate Non-Trigger Voltage	V_{GD}	$V_D = \text{Rated} \times 2/3, T_c = 125^\circ\text{C}$	0.2	—	V
Critical Rate of Rise of Off-State Voltage	dv/dt	$V_{DRM} = \text{Rated} \times 2/3, T_c = 125^\circ\text{C}$ Exponential Rise	100	—	$\text{V}/\mu\text{s}$
Holding Current	I_H	$V_D = 6\text{V}, I_{TM} = 1\text{A}$	—	40	mA
Latching Current	I_L	$V_D = 6\text{V}, f = 50\text{Hz}, t_{gw} = 50\mu\text{s}$ $i_G = 30\text{mA}$	—	60	mA
Thermal Resistance	$R_{th(j-c)}$	Junction to Case	—	3	$^\circ\text{C}/\text{W}$

MARKING

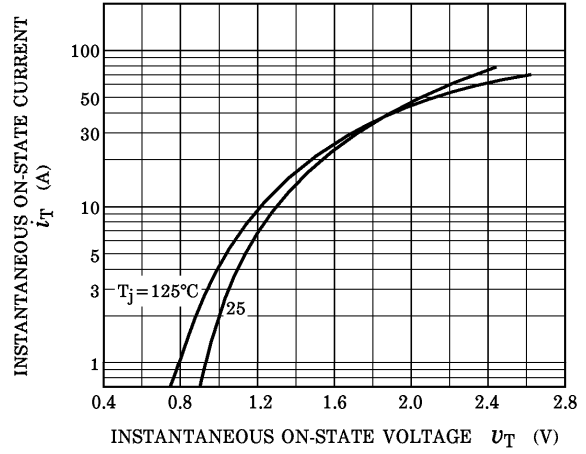


NUMBER	SYMBOL	MARK
※1	TYPE	SF8G41A
		SF8J41A
※2	SF8G41A, SF8J41A	A
※3	Lot Number Month (Starting from Alphabet A) Year (Last Decimal Digit of the Current Year)	Example 8A : January 1998 8B : February 1998 8L : December 1998

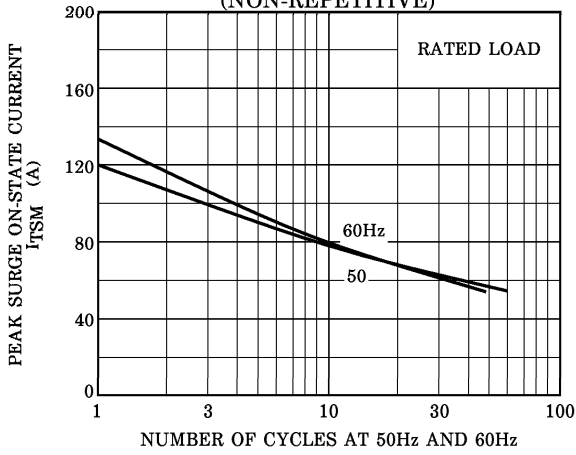
GATE TRIGGER CHARACTERISTIC



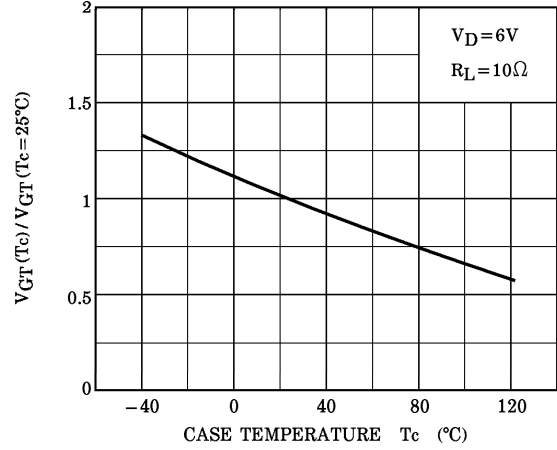
$i_T - v_T$



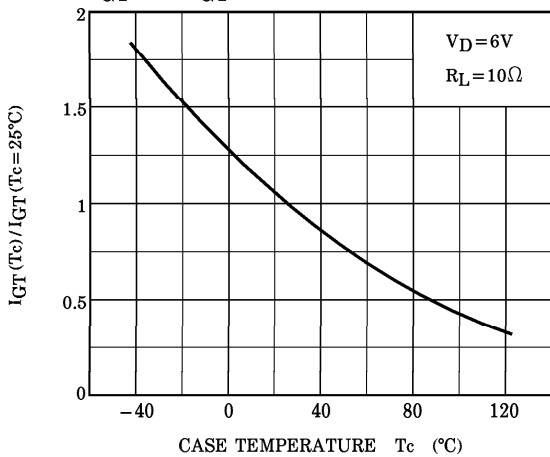
SURGE ON-STATE CURRENT (NON-REPETITIVE)



$V_{GT}(T_c) / V_{GT}(T_c = 25^\circ C) - T_c$ (TYPICAL)



$I_{GT}(T_c) / I_{GT}(T_c = 25^\circ C) - T_c$ (TYPICAL)



$I_H(T_c) / I_H(T_c = 25^\circ C) - T_c$ (TYPICAL)

